SamHop Microelectronics Corp.

STU/D339S

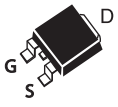
Ver 1.0

N-Channel Logic Level Enhancement Mode Field Effect Transistor

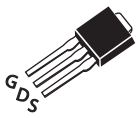
PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
30V	40A	9.6 @ VGS=10V
		15 @ VGS=4.5V

FEATURES

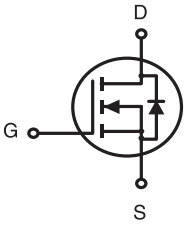
- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- TO-252 and TO-251 Package.



STU SERIES
TO-252AA(D-PAK)



STD SERIES
TO-251(I-PAK)



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V_{DS}	Drain-Source Voltage		30	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Drain Current-Continuous	T_C=25°C	40	A
		T_C=70°C	32	A
I_{DM}	-Pulsed [a]		117	A
E_{AS}	Single Pulse Avalanche Energy [c]		56	mJ
P_D	Maximum Power Dissipation	T_C=25°C	42	W
		T_C=70°C	27	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V , V_{GS}=0V			1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V , V_{DS}=0V			±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=250uA	1.0	1.7	3	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V , I_D=20A		8.2	9.6	m ohm
		V_{GS}=4.5V , I_D=16A		11.5	15	m ohm
g_{FS}	Forward Transconductance	V_{DS}=10V , I_D=20A		55		S
DYNAMIC CHARACTERISTICS [b]						
C_{ISS}	Input Capacitance	V_{DS}=15V,V_{GS}=0V f=1.0MHz		900		pF
C_{OSS}	Output Capacitance			161		pF
C_{RSS}	Reverse Transfer Capacitance			124		pF
SWITCHING CHARACTERISTICS [b]						
$t_{D(ON)}$	Turn-On Delay Time	V_{DD}=15V I_D=1A V_{GS}=10V R_{GEN}= 6 ohm		17		ns
t_r	Rise Time			18		ns
$t_{D(OFF)}$	Turn-Off Delay Time			18		ns
t_f	Fall Time			46		ns
Q_g	Total Gate Charge	V_{DS}=15V,I_D=20A,V_{GS}=10V		14		nC
		V_{DS}=15V,I_D=20A,V_{GS}=4.5V		6.5		nC
Q_{gs}	Gate-Source Charge	V_{DS}=15V,I_D=20A, V_{GS}=10V		1.8		nC
Q_{gd}	Gate-Drain Charge			4.1		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_S=2A		0.77	1.3	V

Notes

a.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
b.Guaranteed by design, not subject to production testing.
c.Starting T_J=25°C,L=0.5mH,V_{DD} = 20V.(See Figure13)

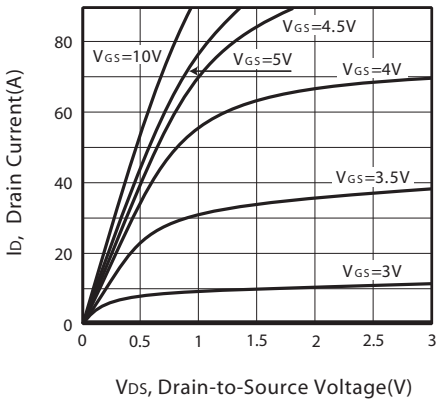


Figure 1. Output Characteristics

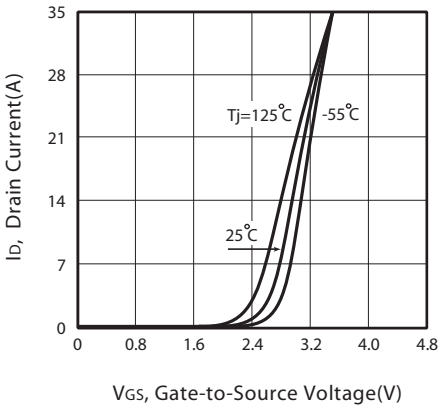


Figure 2. Transfer Characteristics

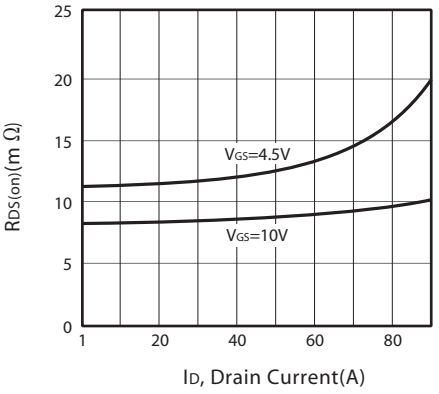


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

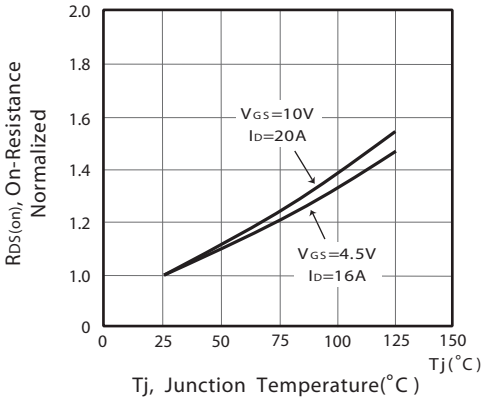


Figure 4. On-Resistance Variation with Drain Current and Temperature

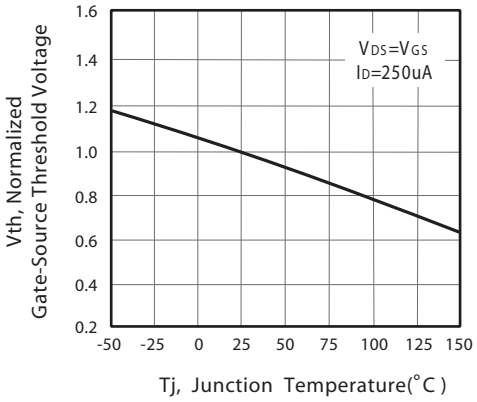


Figure 5. Gate Threshold Variation with Temperature

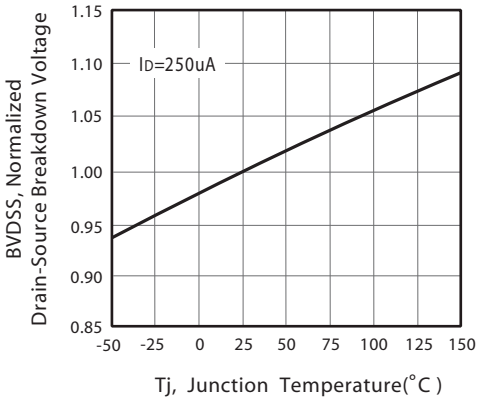


Figure 6. Breakdown Voltage Variation with Temperature

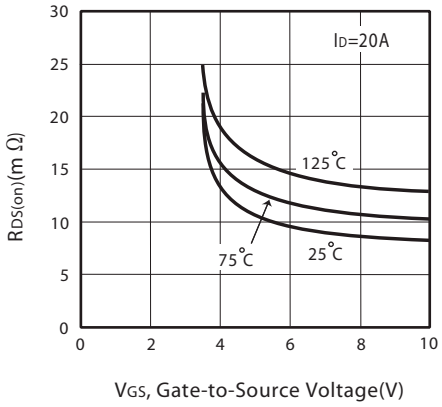


Figure 7. On-Resistance vs. Gate-Source Voltage

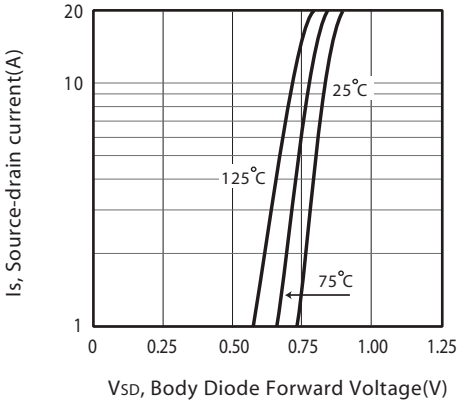


Figure 8. Body Diode Forward Voltage Variation with Source Current

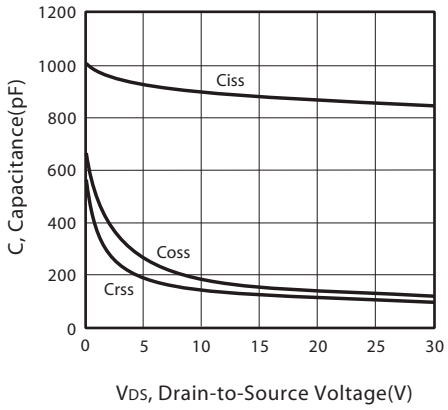


Figure 9. Capacitance

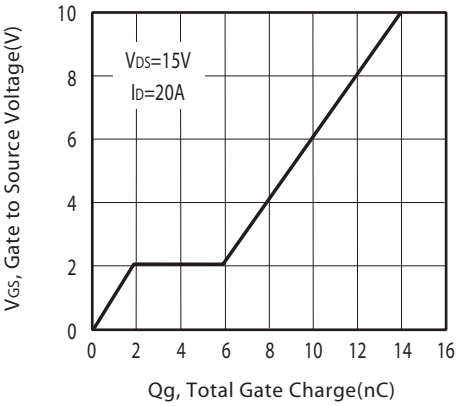


Figure 10. Gate Charge

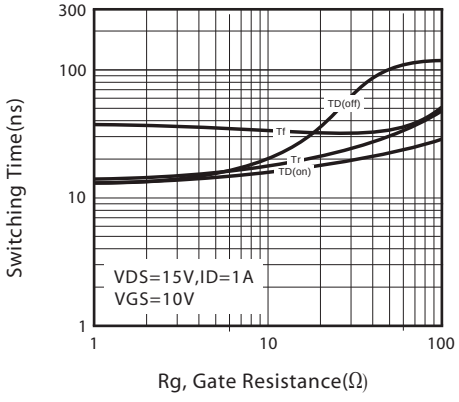


Figure 11. switching characteristics

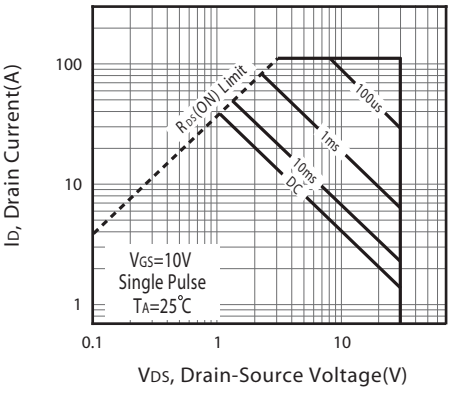
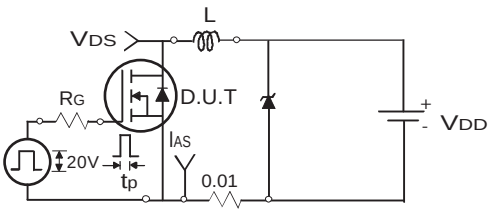
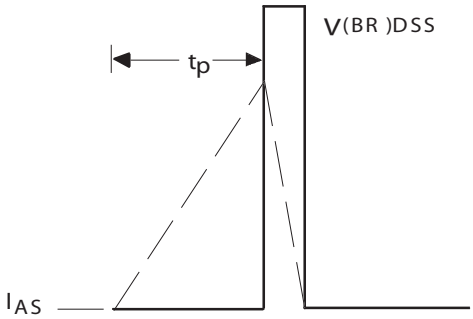


Figure 12. Maximum Safe Operating Area



Uncamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

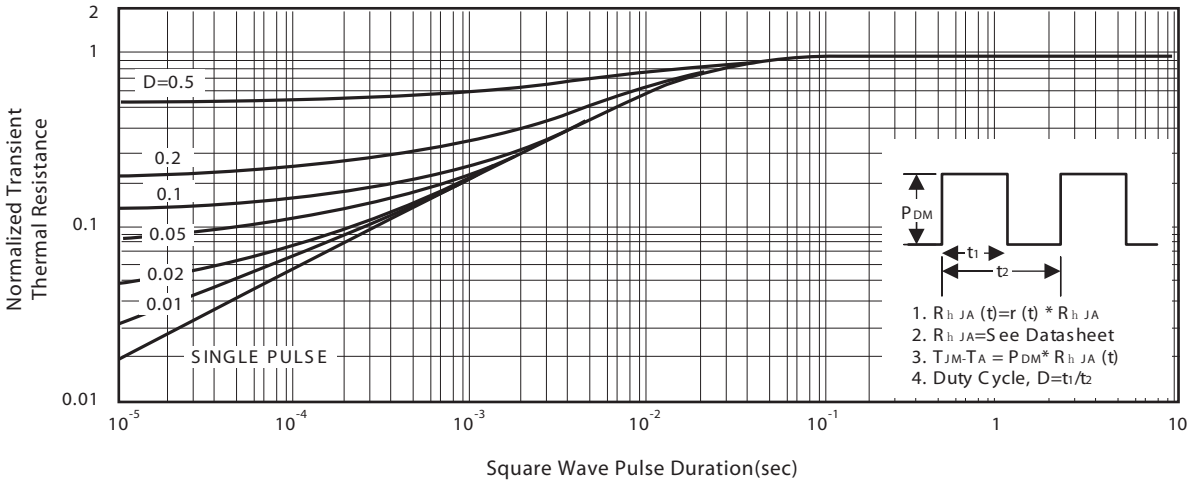
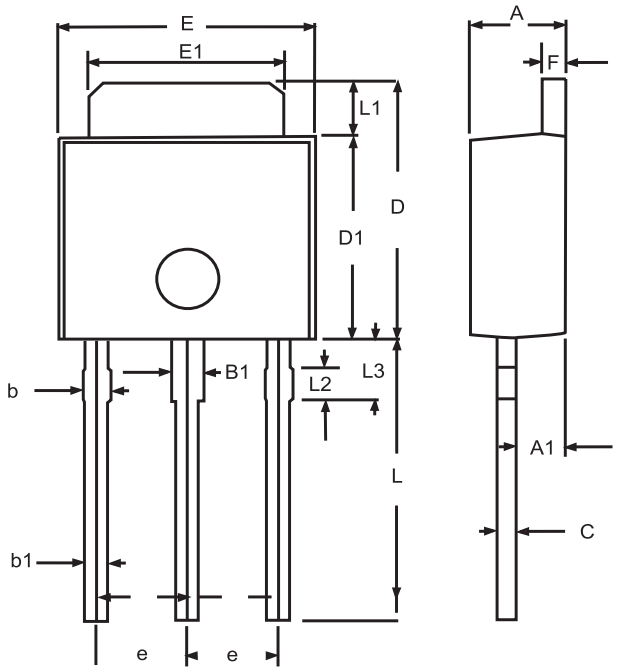


Figure 14. Normalized Thermal Transient Impedance Curve

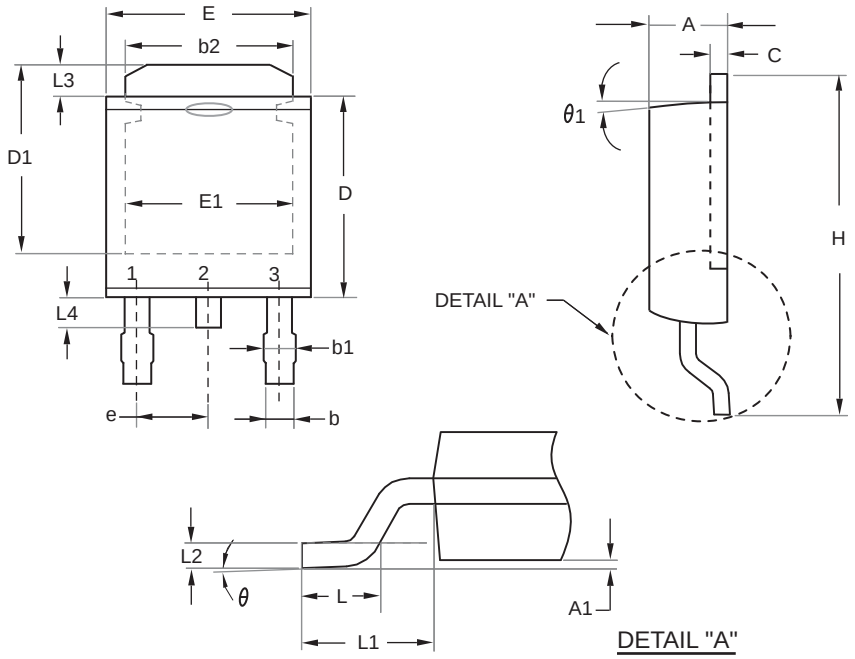
PACKAGE OUTLINE DIMENSIONS

TO-251



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.095
A1	1.100	1.300	0.043	0.051
B1	0.650	1.050	0.026	0.041
b	0.500	0.900	0.020	0.035
b1	0.400	0.800	0.016	0..32
C	0.400	0.600	0.016	0.024
D	6.700	7.300	0.264	0.287
D1	5.400	5.650	0.213	0.222
E	6.40	6.650	0.252	0.262
e	2.100	2.500	0.083	0.098
F	0.400	0.600	0.016	0.024
L	7.000	8.000	0.276	0.315
L1	1.300	1.700	0.051	0.067
L2	0.700	0.900	0.028	0.035
L3	1.400	1.800	0.055	0.071

TO-252

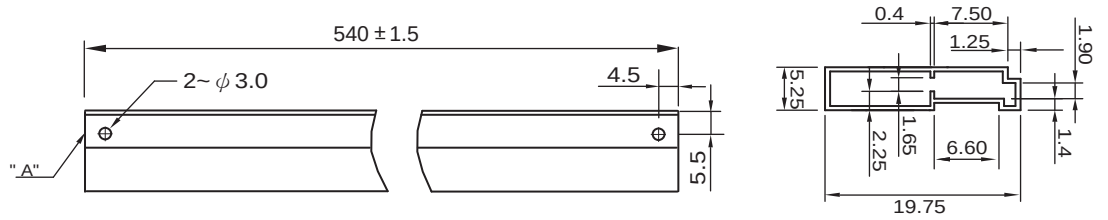


DETAIL "A"

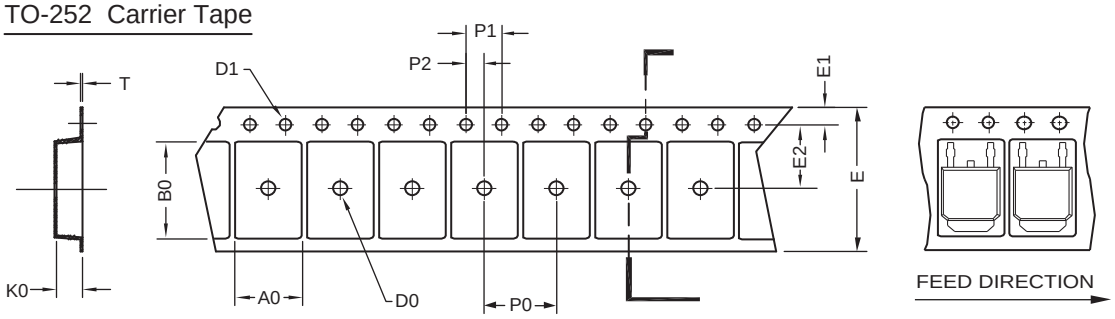
SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.184	2.388	0.086	0.094
A1	0.000	0.127	0.000	0.005
b	0.633	0.889	0.025	0.035
b1	0.666	1.092	0.026	0.043
b2	5.207	5.461	0.205	0.215
C	0.460	0.584	0.018	0.023
D	5.969	6.223	0.235	0.245
D1	5.415	5.515	0.213	0.217
E	6.400	6.731	0.252	0.265
E1	4.902	5.004	0.193	0.197
e	2.286	BSC	0.090	BSC
H	9.601	10.286	0.378	0.405
L	1.313	1.651	0.052	0.065
L1	2.666	3.174	0.105	0.125
L2	0.460	0.560	0.018	0.022
L3	0.889	1.143	0.035	0.045
L4	0.508	1.016	0.020	0.040
θ	0°	8°	0°	8°
θ1	7°	REF.	7°	REF.

TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



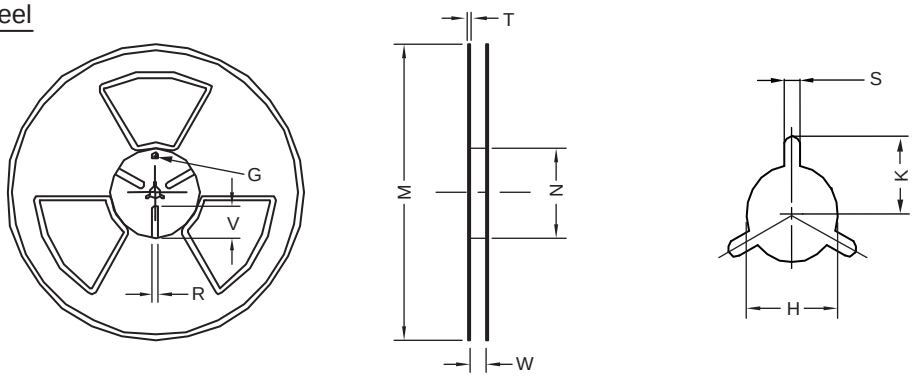
TO-252 Carrier Tape



UNIT:㎜

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 ㎜)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	ϕ 2	ϕ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:㎜

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 ㎜	ϕ 330	ϕ 330 ± 0.5	ϕ 97 ± 1.0	17.0 + 1.5 - 0	2.2	ϕ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---